

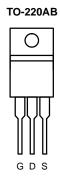
N-Channel 60 V (D-S) MOSFET

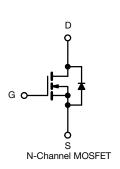
PRODUCT SUMMARY				
V _{DS} (V)	$V_{DS}(V)$ $R_{DS(on)}(\Omega)$			
60	0.005 at V _{GS} = 10 V	120		
	0.008 at $V_{GS} = 7.5 \text{ V}$	100		

FEATURES

- 175 °C Junction Temperature
- TrenchFET® Power MOSFET
- Material categorization:







Parameter		Symbol	Limit	Unit	
Gate-Source Voltage		V _{GS}	± 20	V	
Continuous Drain Current (T _J = 175 °C) ^b	T _C = 25 °C		120		
	T _C = 100 °C	I _D	90		
Pulsed Drain Current	I _{DM}	350	Α		
Continuous Source Current (Diode Conduction)	I _S	70 ^a			
Avalanche Current	I _{AS}	50			
Single Avalanche Energy (Duty Cycle ≤ 1 %)	L = 0.1 mH	E _{AS}	125	mJ	
Mariana Barra Birainatia	T _C = 25 °C	В	136	W	
Maximum Power Dissipation	T _A = 25 °C	P _D	3 ^b , 8.3 ^{b, c}] vv	
Operating Junction and Storage Temperature Range		T _J , T _{stg}	- 55 to 175	°C	

THERMAL RESISTANCE RATINGS							
Parameter		Symbol	Typical	Maximum	Unit		
Maniana la satisma ta Amelianta	t ≤ 10 sec	R _{thJA}	15	18	°C/W		
Maximum Junction-to-Ambient ^a	Steady State		40	50			
Maximum Junction-to-Case		R _{thJC}	0.85	1.1			

Notes:

- a. Package limited.
- b. Surface mounted on 1" x 1" FR4 board.
- $c.\ t \leq 10\ s.$



Parameter	Symbol	Test Conditions		Typ. ^a	Max.	Unit	
Static			l .		<u> </u>		
Drain-Source Breakdown Voltage	V _{DS}	$V_{GS} = 0 \text{ V}, I_D = 250 \mu\text{A}$	60			V	
Gate Threshold Voltage	V _{GS(th)}	$V_{DS} = V_{GS}, I_{D} = 250 \mu A$	2		4		
Gate-Body Leakage	I _{GSS}	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$			± 100	nA	
		V _{DS} = 60 V, V _{GS} = 0 V			1		
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} = 60 V, V _{GS} = 0 V, T _J = 125 °C			50 μA		
		V _{DS} = 60 V, V _{GS} = 0 V, T _J = 175 °C			250	1	
On-State Drain Current ^b	I _{D(on)}	V _{DS} = 5 V, V _{GS} = 10 V	60			Α	
		V _{GS} = 10 V, I _D = 20 A		0.005			
D : 0	D	V _{GS} = 10 V, I _D = 20 A, T _J = 125 °C		0.010		0	
Drain-Source On-State Resistance ^b	R _{DS(on)}	V _{GS} = 10 V, I _D = 20 A, T _J = 175 °C		0.015		Ω	
		$V_{GS} = 7.5 \text{ V}, I_D = 15 \text{ A}$		0.008			
Forward Transconductance ^b	9 _{fs}	$V_{DS} = 15 \text{ V}, I_{D} = 20 \text{ A}$		60		S	
Dynamic			•	•			
Input Capacitance	C _{iss}			6650			
Output Capacitance	C _{oss}	$V_{GS} = 0 \text{ V}, V_{DS} = 25 \text{ V}, f = 1 \text{ MHz}$		570		pF	
Reverse Transfer Capacitance	C _{rss}			325			
Total Gate Charge ^c	Qg			47	70		
Gate-Source Charge ^c	Q_{gs}	$V_{DS} = 30 \text{ V}, V_{GS} = 10 \text{ V}, I_{D} = 50 \text{ A}$		10		nC	
Gate-Drain Charge ^c	Q _{gd}			12			
Turn-On Delay Time ^c	t _{d(on)}			10	20		
Rise Time ^c	t _r	V_{DD} = 30 V, R_L = 0.6 Ω		15	25	20	
Turn-Off Delay Time ^c	t _{d(off)}	$I_D \cong 50 \text{ A}, V_{GEN} = 10 \text{ V}, R_g = 2.5 \Omega$		35	50	ns	
Fall Time ^c	t _f			20	30		
Source-Drain Diode Ratings and Cha	aracteristics (T _C = 25 °C)					
Pulsed Current	I _{SM}			350		Α	
Diode Forward Voltage	V_{SD}	I _F = 20 A, V _{GS} = 0 V		1	1.5	V	
Reverse Recovery Time	t _{rr}	I _F = 20 A, di/dt = 100 A/μs		45	100	ns	

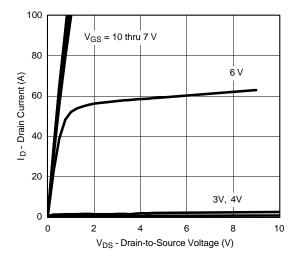
Notes:

- a. For design aid only; not subject to production testing.
- b. Pulse test; pulse width $\leq 300~\mu s,$ duty cycle $\leq 2~\%.$
- c. Independent of operating temperature.

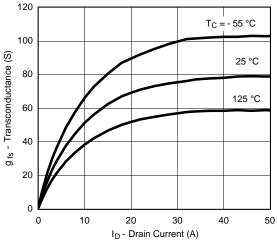
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



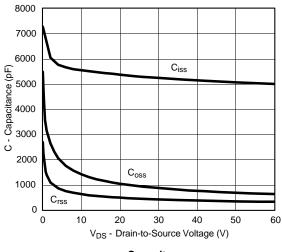
TYPICAL CHARACTERISTICS (25 °C unless noted)



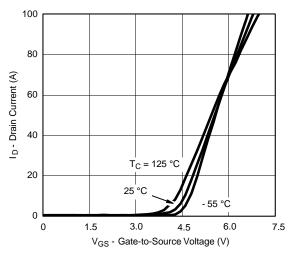
Output Characteristics



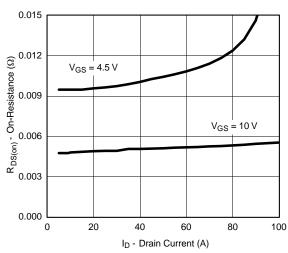
Transconductance



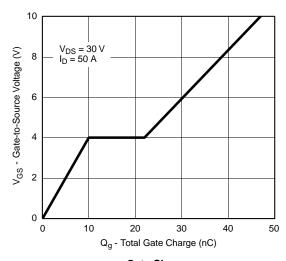
Capacitance



Transfer Characteristics



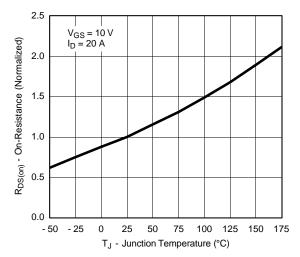
On-Resistance vs. Drain Current



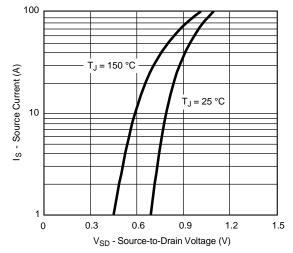
Gate Charge



TYPICAL CHARACTERISTICS (25 °C unless noted)



On-Resistance vs. Junction Temperature



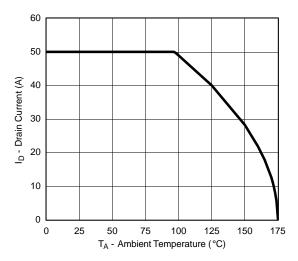
Source-Drain Diode Forward Voltage

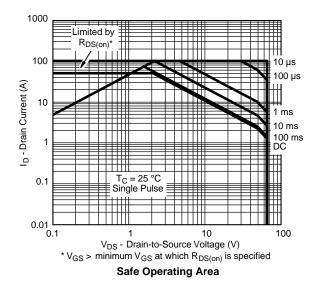
Normalized Effective Transient Thermal Impedance

0.01 10-4



THERMAL RATINGS



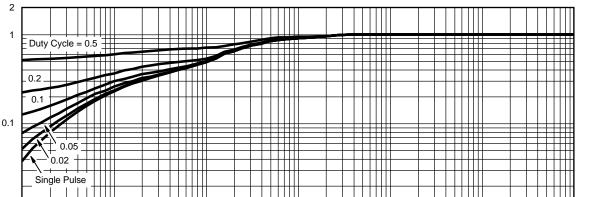


10

100

Maximum Drain Current vs. Ambient Temperature

10-3



Normalized Thermal Transient Impedance, Junction-to-Case

10-1

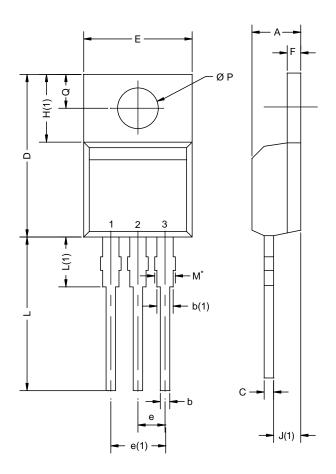
Square Wave Pulse Duration (s)

10-2

5



TO-220AB



	MILLIM	IETERS	INC	HES	
DIM.	MIN.	MAX.	MIN.	MAX.	
Α	4.25	4.65	0.167	0.183	
b	0.69	1.01	0.027	0.040	
b(1)	1.20	1.73	0.047	0.068	
С	0.36	0.61	0.014	0.024	
D	14.85	15.49	0.585	0.610	
Е	10.04	10.51	0.395	0.414	
е	2.41	2.67	0.095	0.105	
e(1)	4.88	5.28	0.192	0.208	
F	1.14	1.40	0.045	0.055	
H(1)	6.09	6.48	0.240	0.255	
J(1)	2.41	2.92	0.095	0.115	
L	13.35	14.02	0.526	0.552	
L(1)	3.32	3.82	0.131	0.150	
ØΡ	3.54	3.94	0.139	0.155	
Q	2.60	3.00	0.102	0.118	
ECN: X12-0208-Rev. N, 08-Oct-12 DWG: 5471					

Notes

 $^{^{\}star}$ M = 1.32 mm to 1.62 mm (dimension including protrusion) Heatsink hole for HVM



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